Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. – 5. (canceled)

6. (presently amended) A thermoelectric package, comprising:

a microelectronic die having at least one area of which is of a higher heat dissipation rate than the remainder of the microelectronic die when in operation;

a first electrode proximate said microelectronic die including said higher heat area;

a dielectric material proximate said first electrode;

a second electrode opposing said first electrode with said dielectric material disposed therebetween; and

a plurality of nano-wires extending between said first electrode and said second electrode, wherein the plurality of nano-wires comprise a higher density proximate to said area of higher heat dissipation rate and a lower density proximate to said remainder of the microelectronic die.

7. (canceled)

8. (original) The package of claim 6, wherein said at least one nano-wire comprises a bismuth containing material.

9. (original) The package of claim 6, wherein said dielectric material comprises a porous dielectric material.

10. (original) The package of claim 9, wherein said porous dielectric material comprises porous alumina.

11. (original) The package of claim 6, further comprising a negatively charged trace electrically connected to said first electrode and a positively charged trace to said second electrode.

12. – 20. (canceled)

21. (presently amended) An electronic system, comprising:

an external substrate within a housing; and

at least one microelectronic device package attached to said external substrate, having at least thermoelectric device including:

a first electrode;

a dielectric material proximate said first electrode;

a second electrode opposing said first electrode with said dielectric material deposed therebetween; and

~~at least one nano-wire~~ a plurality of nano-wires extending between said first electrode and said second electrode, wherein the plurality of nano-wires comprise a higher density proximate to an area of higher heat dissipation rate of the microelectronic die when in operation and a lower density proximate to a remainder of the microelectronic die;

an input device interfaced with said external substrate; and

a display device interfaced with said external substrate.

22. (original) The system of claim 21, wherein said at least one nano-wire comprises a bismuth containing material.

23. (original) The system of claim 21, wherein said dielectric material comprises a porous dielectric material.

24. (original) The system of claim 23, wherein said porous dielectric material comprises porous alumina.

25. (original) The system of claim 21, wherein said thermoelectric device further comprises a negatively charged trace electrically connected to said first electrode and a positively charged trace to said second electrode.